

# Toyohiro Chikyow

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

282 papers	6,425 citations	33 h-index	74 g-index
306 ext. papers	6,864 ext. citations	3.3 avg, IF	5.5 L-index

#	Paper	IF	Citations
282	Quantum Molecular Devices Toward Large-Scale Integration. <i>NIMS Monographs</i> , <b>2022</b> , 181-195	0.3	
281	Effects of Zn x Mn1-x S buffer layer on nonpolar AlN growth on Si (100) substrate. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SCCG02	1.4	
280	Effects of low temperature buffer layer on all-sputtered epitaxial GaN/AlN film on Si (111) substrate. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SCCG03	1.4	0
279	Accelerating two-dimensional X-ray diffraction measurement and analysis with density-based clustering for thin films. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SCCG04	1.4	0
278	Evidence-based recommender system for high-entropy alloys. <i>Nature Computational Science</i> , <b>2021</b> , 1, 470-478		1
277	Development of the Material Sequencer for Automatic Various Evaluations. <i>Journal of Surface Analysis (Online)</i> , <b>2021</b> , 28, 35-45	0.1	
276	Photoelectron spectroscopic study on electronic state of corundum In2O3 epitaxial thin film grown by mist-CVD. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SIIG12	1.4	2
275	Band alignment at non-polar AlN/MnS interface investigated by hard X-ray photoelectron spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SIIG07	1.4	1
274	Layer-by-Layer Motif Heteroarchitecturing of N,S-Codoped Reduced Graphene Oxide-Wrapped Ni/NiS Nanoparticles for the Electrochemical Oxidation of Water. <i>ChemSusChem</i> , <b>2020</b> , 13, 3269-3276	8.3	10
273	Evaluation of Band Alignment of SrNbO2N Using Hard X-ray Photoelectron Spectroscopy. <i>Journal of Physical Chemistry C</i> , <b>2020</b> , 124, 5528-5532	3.8	4
272	Automatic Threshold Prediction of Photoelectron Yield Spectroscopy (PYS) by Machine Learning. <i>Vacuum and Surface Science</i> , <b>2020</b> , 63, 270-276	0	
271	Origin of Fermi level pinning in high-k gate stack structures studied by operando hard x-ray photoelectron spectroscopy. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , <b>2020</b> , 238, 146890	1.7	1
270	Valence Band Modification of a (GaIn)O Solid Solution System Fabricated by Combinatorial Synthesis. <i>ACS Combinatorial Science</i> , <b>2020</b> , 22, 433-439	3.9	6
269	Temperature and polarity dependence of electrical properties of ZnO film on pyroelectric LiNbO3 single crystal. <i>Japanese Journal of Applied Physics</i> , <b>2020</b> , 59, SIIG11	1.4	
268	Mesostructured HfO/AlO Composite Thin Films with Reduced Leakage Current for Ion-Conducting Devices. <i>ACS Omega</i> , <b>2019</b> , 4, 14680-14687	3.9	5
267	Wide band gap kesterite absorbers for thin film solar cells: potential and challenges for their deployment in tandem devices. <i>Sustainable Energy and Fuels</i> , <b>2019</b> , 3, 2246-2259	5.8	11
266	Molecular magnetic thin films made from Ni-Co Prussian blue analogue anchored on silicon wafers. <i>Journal of Magnetism and Magnetic Materials</i> , <b>2019</b> , 486, 165276	2.8	5

265	Reaction mechanism of ZrO <sub>x</sub> metal resists with extreme ultraviolet irradiation. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SDDC01	1.4	1
264	Crystal growth of a MnS buffer layer for non-polar AlN on Si (100) deposited by radio frequency magnetron sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SBBK03	1.4	2
263	Electrical and Structural Properties of the Partial Ternary Thin-Film System Ni-Si-B. <i>ACS Combinatorial Science</i> , <b>2019</b> , 21, 310-315	3.9	2
262	Effects of substrate self-bias and nitrogen flow rate on non-polar AlN film growth by reactive sputtering. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SDDG07	1.4	4
261	Photoelectron spectroscopic study of electronic states and surface structure of an in situ cleaved In <sub>2</sub> O <sub>3</sub> (111) single crystal. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, SDDG06	1.4	5
260	Photoelectron spectroscopic study on electronic state and electrical properties of SnO <sub>2</sub> single crystals. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 080903	1.4	5
259	Validation with Measured Data of Photoelectron Yield Spectroscopy (PYS) Threshold Using Machine Learning. <i>Vacuum and Surface Science</i> , <b>2019</b> , 62, 504-510	0	2
258	Spectroscopic Observation of the Interface States at the SiO <sub>2</sub> /4H-SiC(0001) Interface. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2019</b> , 17, 56-60	0.7	2
257	Device Geometry Engineering for Controlling Organic Antiambipolar Transistor Properties. <i>Journal of Physical Chemistry C</i> , <b>2018</b> , 122, 6943-6946	3.8	24
256	Improved leakage current properties of ZrO <sub>2</sub> /(Ta/Nb)O <sub>x</sub> -Al <sub>2</sub> O <sub>3</sub> /ZrO <sub>2</sub> nanolaminate insulating stacks for dynamic random access memory capacitors. <i>Thin Solid Films</i> , <b>2018</b> , 655, 48-53	2.2	12
255	Mn Self-Doping of Orthorhombic RMnO Perovskites: (RMn)MnO with R = Er-Lu. <i>Inorganic Chemistry</i> , <b>2018</b> , 57, 2773-2781	5.1	12
254	Interface Engineering for Controlling Device Properties of Organic Antiambipolar Transistors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 2762-2767	9.5	20
253	Chemical Synthesis of Multilayered Nanostructured Perovskite Thin Films with Dielectric Features for Electric Capacitors. <i>ACS Applied Nano Materials</i> , <b>2018</b> , 1, 915-921	5.6	9
252	Study of Sn and Mg doping effects on TiO <sub>2</sub> /Ge stack structure by combinatorial synthesis. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 04FJ04	1.4	
251	Graphene-Wrapped Nanoporous Nickel-Cobalt Oxide Flakes for Electrochemical Supercapacitors. <i>ChemistrySelect</i> , <b>2018</b> , 3, 8505-8510	1.8	9
250	Synthesis of Hollow Co-Fe Prussian Blue Analogue Cubes by using Silica Spheres as a Sacrificial Template. <i>ChemistryOpen</i> , <b>2018</b> , 7, 599-603	2.3	15
249	System for Searching Relationship among Physical Properties for Materials Curation <sup>TM</sup> . <i>Vacuum and Surface Science</i> , <b>2018</b> , 61, 200-205	0	2
248	Combinatorial Thin Film Synthesis for Developments of New High Dielectric Constant Thin Film Materials. <i>Transactions of the Materials Research Society of Japan</i> , <b>2018</b> , 43, 249-254	0.2	1

247	Effect of carbon doping on threshold voltage and mobility of In-Si-O thin-film transistors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2018</b> , 36, 061206	1.3	4
246	Multi-Valued Logic Circuits Based on Organic Anti-ambipolar Transistors. <i>Nano Letters</i> , <b>2018</b> , 18, 4355-4359	5	58
245	Formation of a K-In-Se Surface Species by NaF/KF Postdeposition Treatment of Cu(In,Ga)Se Thin-Film Solar Cell Absorbers. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 3581-3589	9.5	70
244	Detection of Micro/Nano Droplet by Galvanic-Coupled Arrays. <i>ECS Transactions</i> , <b>2017</b> , 75, 51-59	1	11
243	Photoelectron spectroscopic study on monolayer pentacene thin-film/polar ZnO single-crystal hybrid interface. <i>Applied Physics Express</i> , <b>2017</b> , 10, 025702	2.4	3
242	Crystallographic polarity effect of ZnO on thin film growth of pentacene. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 04CJ03	1.4	2
241	Negative Differential Resistance Transistor with Organic p-n Heterojunction. <i>Advanced Electronic Materials</i> , <b>2017</b> , 3, 1700106	6.4	44
240	Polymer/Metal composite for flexible interconnect : Conductive, flexible, adhesive and productive material <b>2017</b> ,		1
239	Photoelectron spectroscopic study of electronic state and surface structure of In <sub>2</sub> O <sub>3</sub> single crystals. <i>Applied Physics Express</i> , <b>2017</b> , 10, 011102	2.4	6
238	Polarization modulation of nanotrenches in GaN (0001)/ $\bar{1}\bar{1}\bar{1}$ by surface hydrogenation. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 111002	1.4	1
237	Cyanide bridged coordination polymer nanoflakes thermally derived Ni <sub>3</sub> C and fcc-Ni nanoparticles for electrocatalysts. <i>New Journal of Chemistry</i> , <b>2017</b> , 41, 14890-14897	3.6	14
236	Recent advances in Prussian blue and Prussian blue analogues: synthesis and thermal treatments. <i>Coordination Chemistry Reviews</i> , <b>2017</b> , 352, 328-345	23.2	152
235	Present status of the materials informatics and its challenge for future materials science. <i>Journal of the Japan Society of Information and Knowledge</i> , <b>2017</b> , 27, 297-304	0.1	1
234	Effect of Y and Mn doping into rutile type TiO <sub>2</sub> /Ge stack structure by combinatorial synthesis. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 06GF11	1.4	2
233	Improvement in ferroelectricity of Hf <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> thin films using ZrO <sub>2</sub> seed layer. <i>Applied Physics Express</i> , <b>2017</b> , 10, 081501	2.4	43
232	Vertical resonant tunneling transistors with molecular quantum dots for large-scale integration. <i>Nanoscale</i> , <b>2017</b> , 9, 11297-11302	7.7	4
231	Prediction of optically-active transitions in type-VIII guest-free silicon clathrate Si <sub>46</sub> : A comparative study of its physical properties with type-I counterpart through first-principles. <i>Journal of Applied Physics</i> , <b>2017</b> , 122, 205103	2.5	7
230	Synergetic nanoporous Mn <sub>2</sub> O <sub>3</sub> oxides as efficient electrocatalysts for the oxygen reduction reaction. <i>New Journal of Chemistry</i> , <b>2017</b> , 41, 8196-8202	3.6	3

229	P-type polymer-based Ag <sub>2</sub> S atomic switch for logic operation. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 06GF03	1.4	5
228	Influence of chemical equilibrium in introduced oxygen vacancies on resistive switching in epitaxial Pt-CeO <sub>2</sub> system. <i>Journal of Solid State Electrochemistry</i> , <b>2017</b> , 21, 657-664	2.6	3
227	(Invited) Conductive Polymer/Metal Composite for Filling of TSV. <i>ECS Transactions</i> , <b>2017</b> , 80, 205-214	1	
226	Direct Observation of the Energy Distribution of Interface States at SiO <sub>2</sub> /4H-SiC Interface: Operando Hard X-ray Photoelectron Spectroscopic Study. <i>Hyomen Kagaku</i> , <b>2017</b> , 38, 347-350		
225	Resistive switching characteristics in memristors with Al <sub>2</sub> O <sub>3</sub> /TiO <sub>2</sub> and TiO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> bilayers. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 08PB02	1.4	17
224	Improvement of the effective work function and transmittance of thick indium tin oxide/ultrathin ruthenium doped indium oxide bilayers as transparent conductive oxide. <i>Thin Solid Films</i> , <b>2016</b> , 598, 126-130	2.2	2
223	Interface stability of electrode/Bi-containing relaxor ferroelectric oxide for high-temperature operational capacitor. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 06GJ12	1.4	1
222	Investigation of new stacking surface passivation structures with interfacial tuning layers on p-type crystalline silicon. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 04ES03	1.4	
221	Thin-film growth of (110) rutile TiO <sub>2</sub> on (100) Ge substrate by pulsed laser deposition. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 06GG06	1.4	1
220	Bottom-electrode effect on switching behavior and interface reaction in nanoionic-based resistive changing memory. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 08PC03	1.4	1
219	Interfacial charge transfer behavior of conducting polymers as contact electrode for semiconductor devices. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 04EC10	1.4	
218	Screening charge localization at LiNbO <sub>3</sub> surface with Schottky junction. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 171604	3.4	
217	Perspective: Highly ordered MoS <sub>2</sub> thin films grown by multi-step chemical vapor deposition process. <i>APL Materials</i> , <b>2016</b> , 4, 030901	5.7	25
216	Adhesion of silver/polypyrrole nanocomposite coating to a fluoropolymer substrate. <i>Applied Surface Science</i> , <b>2016</b> , 384, 492-496	6.7	13
215	BaTiO <sub>3</sub> based relaxor ferroelectric epitaxial thin-films for high-temperature operational capacitors. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 04DH02	1.4	9
214	Combinatorial synthesis of BaTiO <sub>3</sub> Bi(Mg <sub>2</sub> /3Nb <sub>1</sub> /3)O <sub>3</sub> thin-films for high-temperature capacitors. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 06FJ02	1.4	3
213	Bias induced Cu ion migration behavior in resistive change memory structure observed by hard X-ray photoelectron spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 06FG01	1.4	3
212	Interface engineering for improving optical switching in a diarylethene-channel transistor. <i>Organic Electronics</i> , <b>2015</b> , 21, 149-154	3.5	20

211	Ge incorporated epitaxy of (110) rutile TiO <sub>2</sub> on (100) Ge single crystal at low temperature by pulsed laser deposition. <i>Thin Solid Films</i> , <b>2015</b> , 591, 105-110	2.2	8
210	Epitaxial growth of high dielectric constant lead-free relaxor ferroelectric for high-temperature operational film capacitor. <i>Thin Solid Films</i> , <b>2015</b> , 592, 29-33	2.2	6
209	Spectroscopic and crystallographic anomalies of (Co <sub>1-x</sub> Zn <sub>x</sub> )Al <sub>2</sub> O <sub>4</sub> spinel oxide. <i>Dalton Transactions</i> , <b>2015</b> , 44, 997-1008	4.3	9
208	Conductive polymer/metal composites for interconnect of flexible devices. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 06FJ12	1.4	8
207	Nanochannel effect in polymer nanowire transistor with highly aligned polymer chains. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 243301	3.4	8
206	Influence of Al <sub>2</sub> O <sub>3</sub> layer insertion on the electrical properties of Ga-In-Zn-O thin-film transistors. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2015</b> , 33, 061506	2.9	6
205	Heteroepitaxial growth of nonpolar Cu-doped ZnO thin film on MnS-buffered (100) Si substrate. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 06FJ10	1.4	1
204	Development of a Simple Probe for Non-Destructive Reversible Electric Contact to nm-Thick Films and 2D Films. <i>E-Journal of Surface Science and Nanotechnology</i> , <b>2015</b> , 13, 307-311	0.7	1
203	Development of Optical Fiber built-in Type Kelvin Probe&mdash;Development of Band Diagram Measurement System&mdash;. <i>Journal of the Vacuum Society of Japan</i> , <b>2015</b> , 58, 144-146		1
202	Reaction factors for photo-electrochemical deposition of metal silver on polypyrrole as conducting polymer. <i>Electrochimica Acta</i> , <b>2015</b> , 183, 15-19	6.7	3
201	Surface passivation of crystalline silicon by sputtered AlO <sub>x</sub> /AlN <sub>x</sub> stacks toward low-cost high-efficiency silicon solar cells. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 08KD18	1.4	3
200	Relationship between passivation properties and band alignment in O <sub>3</sub> -based atomic-layer-deposited AlO <sub>x</sub> on crystalline Si for photovoltaic applications. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 08KD19	1.4	5
199	Channel shape and interpoly dielectric material effects on electrical characteristics of floating-gate-type three-dimensional fin channel flash memories. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 04DD04	1.4	2
198	Multilevel Operation of Resonant Tunneling with Binary Molecules in a MetalInsulatorSemiconductor Configuration. <i>Journal of Physical Chemistry C</i> , <b>2014</b> , 118, 6467-6472	3.8	6
197	Novel method for the prediction of an interface bonding species at alumina/metal interfaces. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2014</b> , 32, 021102	2.9	9
196	Diffusion barrier and adhesion properties of SiO(x)N(y) and SiO(x) layers between Ag/polypyrrole composites and Si substrates. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 9201-6	9.5	7
195	Photoelectron spectroscopic study on band alignment of poly(3-hexylthiophene-2,5-diyl)/polar-ZnO heterointerface. <i>Thin Solid Films</i> , <b>2014</b> , 554, 194-198	2.2	3
194	Optically controllable dual-gate organic transistor produced via phase separation between polymer semiconductor and photochromic spiropyran molecules. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 10415-20	9.5	21



193	Improved thermal stability in photochromism-based optically controllable organic thin film transistor. <i>Organic Electronics</i> , <b>2014</b> , 15, 1891-1895	3.5	4
192	Bias-Dependence Potential Distribution in Gate Stack Structuresby Hard-X-ray Photoelectron Spectroscopy under Device Operation. <i>Hyomen Kagaku</i> , <b>2014</b> , 35, 361-364		
191	A Numerical Formula for General Prediction of Interface Bonding between Alumina and Aluminum-Containing Alloys. <i>International Journal of Metals</i> , <b>2014</b> , 2014, 1-11		6
190	Comparative Study of Charge Trapping Type SOI-FinFET Flash Memories with Different Blocking Layer Materials. <i>Journal of Low Power Electronics and Applications</i> , <b>2014</b> , 4, 153-167	1.7	4
189	Epitaxial growth of nonpolar ZnO and n-ZnO/i-ZnO/p-GaN heterostructure on Si(001) for ultraviolet light emitting diodes. <i>Applied Physics Express</i> , <b>2014</b> , 7, 062102	2.4	12
188	Influence of the substrate choice on the L10 phase formation of post-annealed Pt/Fe and Pt/Ag/Fe thin films. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 044310	2.5	12
187	Detailed study of the effects of interface properties of ozone-based atomic layer deposited AlOx on the surface passivation of crystalline silicon. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 04ER06	1.4	2
186	Through silicon via filling methods with metal/polymer composite for three-dimensional LSI. <i>Japanese Journal of Applied Physics</i> , <b>2014</b> , 53, 06JH01	1.4	15
185	Optically and electrically driven organic thin film transistors with diarylethene photochromic channel layers. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 3625-30	9.5	71
184	Photoisomerization-induced manipulation of single-electron tunneling for novel Si-based optical memory. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 11371-6	9.5	12
183	Unique device operations by combining optical-memory effect and electrical-gate modulation in a photochromism-based dual-gate transistor. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2013</b> , 5, 9726-31	9.5	34
182	Epitaxial CeO <sub>2</sub> thin films for a mechanism study of resistive random access memory (ReRAM). <i>Journal of Solid State Electrochemistry</i> , <b>2013</b> , 17, 3137-3144	2.6	7
181	Cathodoluminescence and field emission from GaN/MgAl <sub>2</sub> O <sub>4</sub> grown by metalorganic chemical vapor deposition: substrate-orientation dependence. <i>Journal of Materials Chemistry C</i> , <b>2013</b> , 1, 238-245	7.1	5
180	Optical switching of carrier transport in polymeric transistors with photochromic spiropyran molecules. <i>Journal of Materials Chemistry C</i> , <b>2013</b> , 1, 3012	7.1	53
179	Photoelectron spectroscopic study of band alignment of polymer/ZnO photovoltaic device structure. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 043302	3.4	24
178	Generalized mechanism of the resistance switching in binary-oxide-based resistive random-access memories. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	45
177	Combinatorial synthesis of Cu/(Ta(x)Nb(1-x)) <sub>2</sub> O <sub>5</sub> stack structure for nanoionics-type ReRAM device. <i>ACS Combinatorial Science</i> , <b>2013</b> , 15, 435-8	3.9	5
176	Synthesis of Polystyrene Nanowires Doped with Iron Oxide Nanoparticles Using a Pulsed Laser. <i>Applied Physics Express</i> , <b>2013</b> , 6, 045004	2.4	1

175	Strong Adhesion of Silver/Polypyrrole Composite onto Plastic Substrates toward Flexible Electronics. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 06GG12	1.4	8
174	Bias-voltage application in a hard x-ray photoelectron spectroscopic study of the interface states at oxide/Si(100) interfaces. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 163707	2.5	16
173	Influence of the annealing atmosphere on the structural properties of FePt thin films. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 164314	2.5	15
172	Fast Infilling of TSV with Dispersion of Conductive Polymer/Metal Composite. <i>Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan</i> , <b>2013</b> , 64, 685-686	0.1	
171	Adhesion of Metal-Encrusted Polymer to Plastic Substrates. <i>Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan</i> , <b>2013</b> , 64, 146-147	0.1	
170	Reduction of interfacial SiO <sub>2</sub> at HfO <sub>2</sub> /Si interface with Ta <sub>2</sub> O <sub>5</sub> cap. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 014106	2.5	4
169	Influence of oxygen transfer in Hf-based high-k dielectrics on flatband voltage shift. <i>Thin Solid Films</i> , <b>2012</b> , 520, 3387-3391	2.2	7
168	Effect of niobium doping on the optical and electrical properties in titanium dioxide grown by pulsed laser deposition. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 050603	1.3	5
167	Observation of filament formation process of Cu/HfO <sub>2</sub> /Pt ReRAM structure by hard x-ray photoelectron spectroscopy under bias operation. <i>Journal of Materials Research</i> , <b>2012</b> , 27, 869-878	2.5	5
166	Fermi level of a conducting organic polymer formed on an n-type semiconductor by the photo-electrochemical method. <i>Electrochimica Acta</i> , <b>2012</b> , 82, 378-383	6.7	3
165	Interface engineering for the passivation of c-Si with O <sub>3</sub> -based atomic layer deposited AlO <sub>x</sub> for solar cell application. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 143901	3.4	28
164	Combinatorial Synthesis Study of Passivation Layers for Solar Cell Applications. <i>Materials Science Forum</i> , <b>2012</b> , 725, 161-164	0.4	3
163	Fast Formation of Conductive Material by Simultaneous Chemical Process for Infilling Through-Silicon Via. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FG11	1.4	7
162	Hard x-ray photoelectron spectroscopy study on band alignment at poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/ZnO interface. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 173303	3.4	20
161	Potential of Directed- and Self-Assembled Molecular Nanowires for Optoelectronic Functional Devices. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FA01	1.4	3
160	Fast Formation of Conductive Material by Simultaneous Chemical Process for Infilling Through-Silicon Via. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 06FG11	1.4	4
159	A Novel Formula for General Prediction of an Interface Bonding Species between Alumina and Metal. <i>Journal of the Vacuum Society of Japan</i> , <b>2012</b> , 55, 85-88		3
158	A Formula for Predicting the Effect of Al Alloying on Interface Bonding between Alumina and Metal. <i>Journal of the Vacuum Society of Japan</i> , <b>2012</b> , 55, 233-236		1



157	XPS study of Sb-/In-doping and surface pinning effects on the Fermi level in SnO <sub>2</sub> (101) thin films. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 232107	3.4	37
156	Depletion of the In <sub>2</sub> O <sub>3</sub> (001) and (111) surface electron accumulation by an oxygen plasma surface treatment. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 172101	3.4	62
155	Energy-level alignments and photo-induced carrier processes at the heteromolecular interface of quaterylene and N,N'-dioctyl-3,4,9,10-perylenedicarboximide. <i>Physical Chemistry Chemical Physics</i> , <b>2011</b> , 13, 6280-5	3.6	24
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